

L-7114PWC WHITE

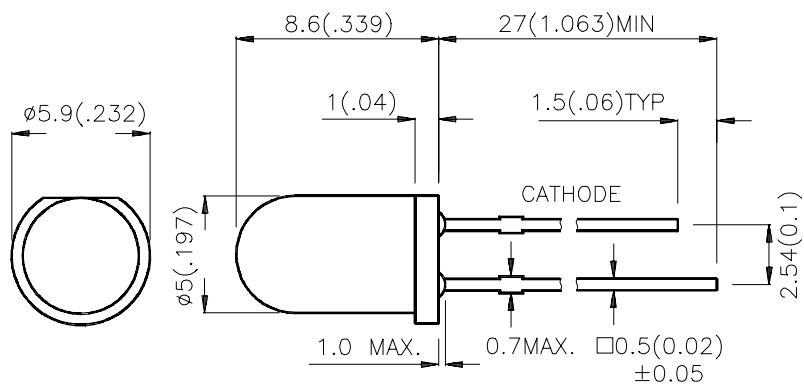
Features

- HIGH EFFICIENCY.
- WHITE EMISSION,HIGH LUMINOUS INTENSITY.

Description

The source color devices are made with InGaN on SiC Light Emitting Diode.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25 (0.01)$ unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Optical Characteristics

Part No.	Dice	Lens Type	Iv (mcd) @ 20 mA		Viewing Angle
			Min.	Typ.	2θ1/2
L-7114PWC	WHITE (InGaN)	WATER CLEAR	500	1000	20°

Note:

1. θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.

Electrical / Optical Characteristics at T_A=25°C

Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
V _F	Forward Voltage	White	3.6	4.2	V	IF=20mA
I _R	Reverse Current	White		10	uA	VR = 5V
X	Chromaticity Coordinates	White	0.33			
Y			0.36			
C	Capacitance	White	65		pF	VF=0V, f =1MHz

Absolute Maximum Ratings at T_A=25°C

Parameter	White	Units
Power dissipation	102	mW
DC Forward Current	30	mA
Peak Forward Current[1]	150	mA
Reverse Voltage	5	V
Operating Temperature	-40°C To +85°C	
Storage Temperature	-40°C To +85°C	
Lead Solder Temperature[2]	260°C For 5 Seconds	

Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.

2. 4mm below package base.

White L-7114PWC

